DOI: 10.1038/s41467-017-01621-1

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# Publisher Correction: Interlayer excitons in a bulk van der Waals semiconductor

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*Nature Communications* **8**:639 doi:10.1038/s41467-017-00691-5; Article published online: 21 September 2017

In the PDF version of this article, Equation 1 is missing an epsilon at the beginning. The correct version of Equation 1 is below. The HTML version of the paper was correct from the time of publication.

$$\epsilon(E) = (n_\mathrm{b} + \mathrm{i}k_\mathrm{b})^2 + \frac{A}{E_0^2 - E^2 - \mathrm{i}\gamma E}.$$

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